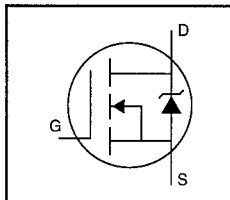


HEXFET® Power MOSFET

- Surface Mount
- Available in Tape & Reel
- Dynamic dv/dt Rating
- Repetitive Avalanche Rated
- Fast Switching
- Ease of Paralleling
- Simple Drive Requirements



$$V_{DSS} = 500V$$

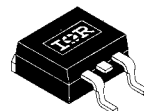
$$R_{DS(on)} = 1.5\Omega$$

$$I_D = 4.5A$$

Description

Third Generation HEXFETs from International Rectifier provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The SMD-220 is a surface mount power package capable of accommodating die sizes up to HEX-4. It provides the highest power capability and the lowest possible on-resistance in any existing surface mount package. The SMD-220 is suitable for high current applications because of its low internal connection resistance and can dissipate up to 2.0W in a typical surface mount application.



SMD-220

Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10 V$	4.5	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10 V$	2.9	
I_{DM}	Pulsed Drain Current ①	18	
$P_D @ T_C = 25^\circ C$	Power Dissipation	74	W
$P_D @ T_A = 25^\circ C$	Power Dissipation (PCB Mount)**	3.1	
	Linear Derating Factor	0.59	W/°C
	Linear Derating Factor (PCB Mount)**	0.025	
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy ②	280	mJ
I_{AR}	Avalanche Current ①	4.5	A
E_{AR}	Repetitive Avalanche Energy ①	7.4	mJ
dv/dt	Peak Diode Recovery dv/dt ③	3.5	V/ns
T_J, T_{STG}	Junction and Storage Temperature Range	-55 to +150	°C
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	

Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	—	1.7	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB mount)**	—	—	40	
$R_{\theta JA}$	Junction-to-Ambient	—	—	62	

** When mounted on 1" square PCB (FR-4 or G-10 Material).

For recommended footprint and soldering techniques refer to application note #AN-994.

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Test Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	500	—	—	V	$V_{GS}=0\text{V}$, $I_D=250\mu\text{A}$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.61	—	V/ $^\circ\text{C}$	Reference to 25°C , $I_D=1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	1.5	Ω	$V_{GS}=10\text{V}$, $I_D=2.7\text{A}$ ④
$V_{GS(th)}$	Gate Threshold Voltage	2.0	—	4.0	V	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$
g_{fs}	Forward Transconductance	2.5	—	—	S	$V_{DS}=50\text{V}$, $I_D=2.7\text{A}$ ④
I_{DSS}	Drain-to-Source Leakage Current	—	—	25	μA	$V_{DS}=500\text{V}$, $V_{GS}=0\text{V}$ $V_{DS}=400\text{V}$, $V_{GS}=0\text{V}$, $T_J=125^\circ\text{C}$
		—	—	250		
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS}=20\text{V}$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS}=-20\text{V}$
Q_g	Total Gate Charge	—	—	38	nC	$I_D=3.1\text{A}$
Q_{gs}	Gate-to-Source Charge	—	—	5.0		$V_{DS}=400\text{V}$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	—	22		$V_{GS}=10\text{V}$ See Fig. 6 and 13 ④
$t_{d(on)}$	Turn-On Delay Time	—	8.2	—	ns	$V_{DD}=250\text{V}$ $I_D=3.1\text{A}$ $R_G=12\Omega$ $R_D=79\Omega$ See Figure 10 ④
t_r	Rise Time	—	16	—		
$t_{d(off)}$	Turn-Off Delay Time	—	42	—		
t_f	Fall Time	—	16	—		
L_D	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6 mm (0.25in.) from package and center of die contact
L_S	Internal Source Inductance	—	7.5	—		
C_{iss}	Input Capacitance	—	610	—	pF	$V_{GS}=0\text{V}$ $V_{DS}=25\text{V}$ $f=1.0\text{MHz}$ See Figure 5
C_{oss}	Output Capacitance	—	160	—		
C_{rss}	Reverse Transfer Capacitance	—	68	—		



Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Test Conditions
I_S	Continuous Source Current (Body Diode)	—	—	4.5	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	18		
V_{SD}	Diode Forward Voltage	—	—	1.6	V	$T_J=25^\circ\text{C}$, $I_S=4.5\text{A}$, $V_{GS}=0\text{V}$ ④
t_{rr}	Reverse Recovery Time	—	320	640	ns	$T_J=25^\circ\text{C}$, $I_F=3.1\text{A}$
Q_{rr}	Reverse Recovery Charge	—	1.0	2.0	μC	$di/dt=100\text{A}/\mu\text{s}$ ④
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D)				

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature (See Figure 11)
- ② $V_{DD}=50\text{V}$, starting $T_J=25^\circ\text{C}$, $L=24\text{mH}$, $R_G=25\Omega$, $I_{AS}=4.5\text{A}$ (See Figure 12)
- ③ $I_{SD}\leq 4.5\text{A}$, $di/dt\leq 75\text{A}/\mu\text{s}$, $V_{DD}\leq V_{(BR)DSS}$, $T_J\leq 150^\circ\text{C}$
- ④ Pulse width $\leq 300\mu\text{s}$; duty cycle $\leq 2\%$.

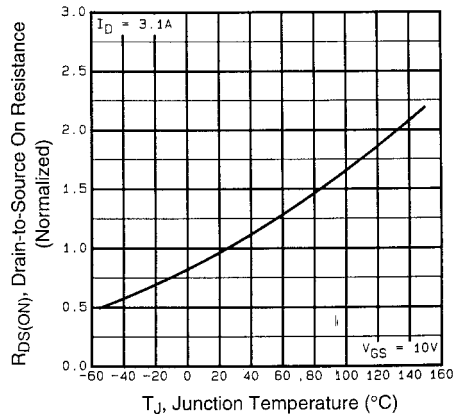
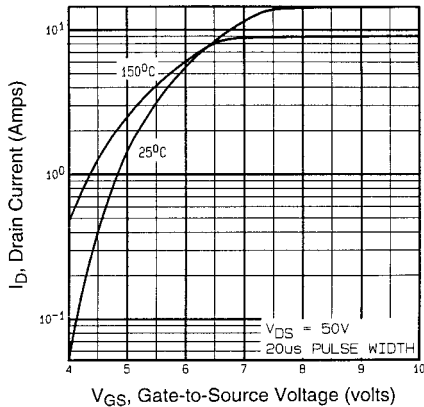
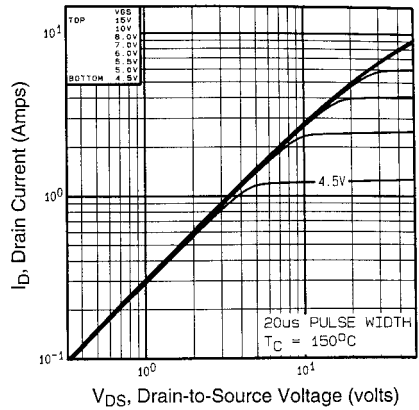
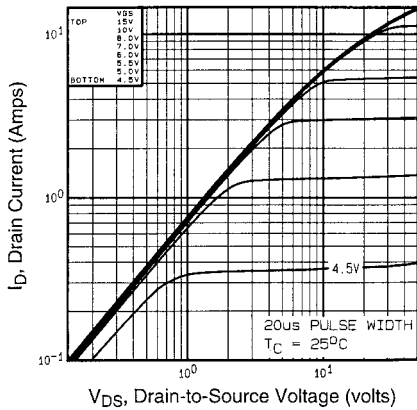


Fig 3. Typical Transfer Characteristics

Fig 4. Normalized On-Resistance Vs. Temperature

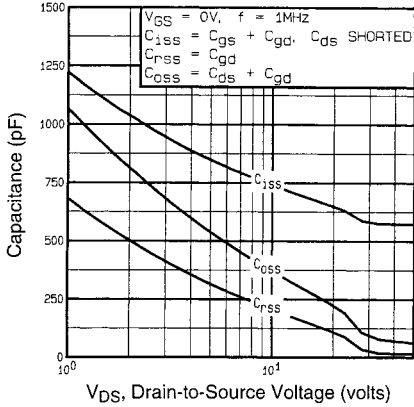


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

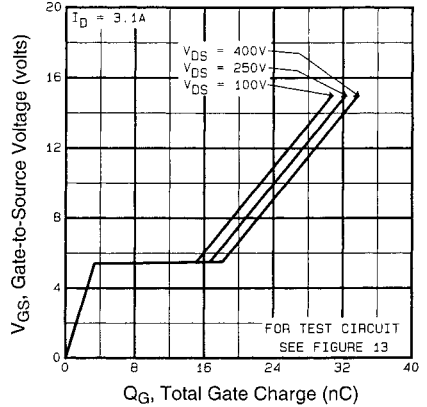


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

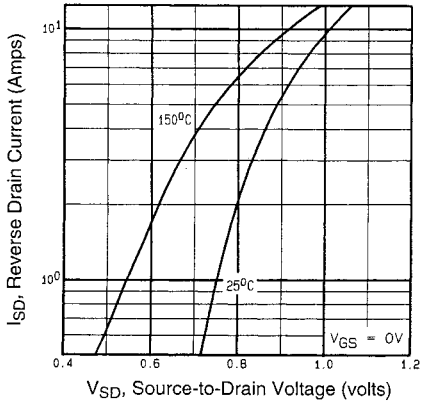


Fig 7. Typical Source-Drain Diode Forward Voltage

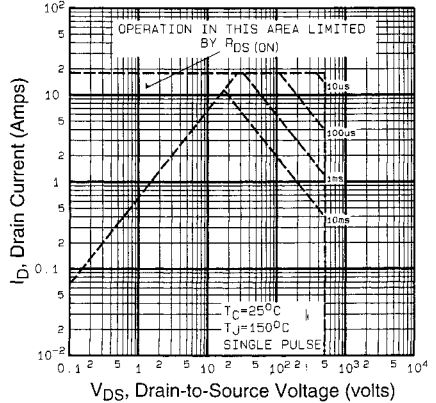


Fig 8. Maximum Safe Operating Area

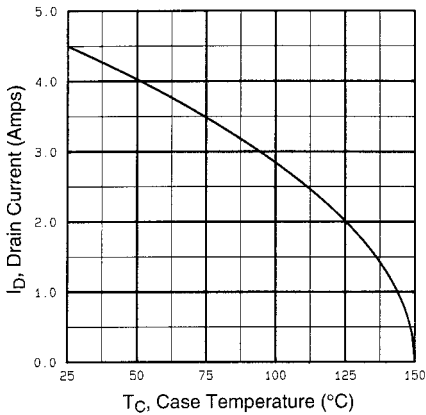


Fig 9. Maximum Drain Current Vs. Case Temperature

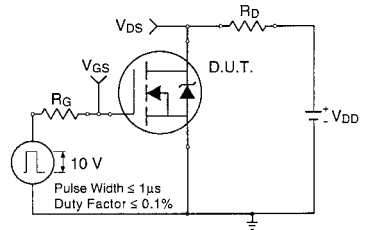


Fig 10a. Switching Time Test Circuit

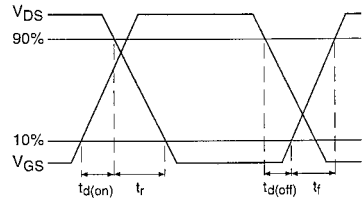


Fig 10b. Switching Time Waveforms

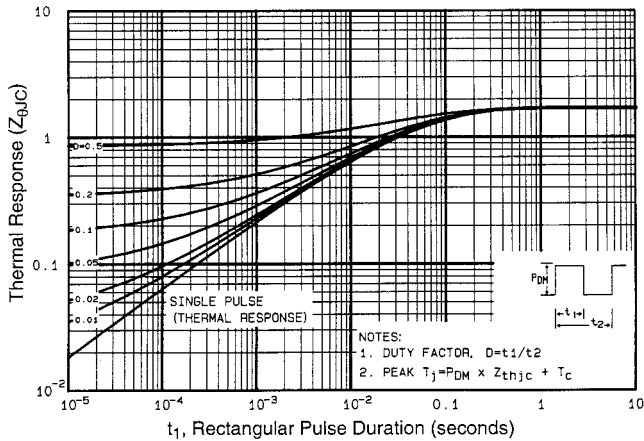


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

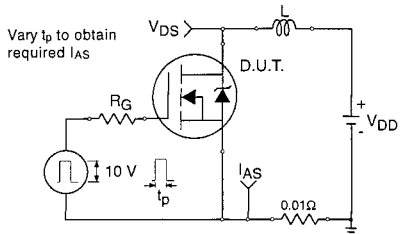


Fig 12a. Unclamped Inductive Test Circuit

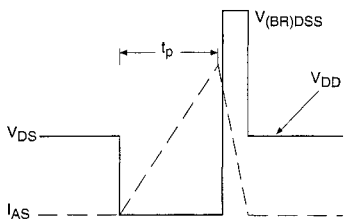


Fig 12b. Unclamped Inductive Waveforms

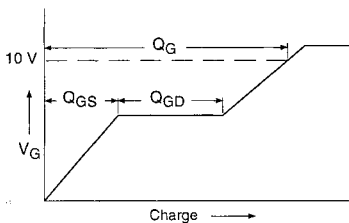


Fig 13a. Basic Gate Charge Waveform

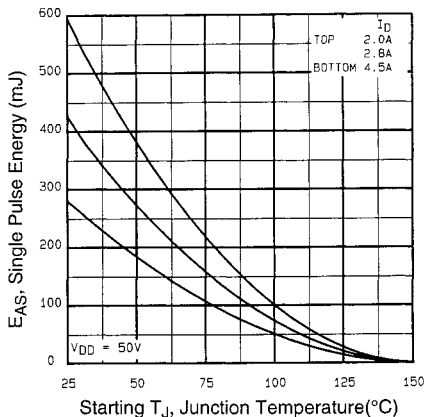


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

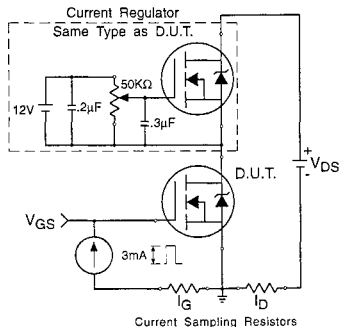


Fig 13b. Gate Charge Test Circuit

Appendix A: Figure 14, Peak Diode Recovery dv/dt Test Circuit

Appendix B: Package Outline Mechanical Drawing

Appendix C: Part Marking Information

Appendix D: Tape & Reel Information